

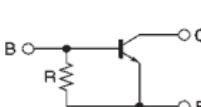
Digital transistors (built-in resistor)

DTC115GUA / DTC115GKA

●Features

- 1) The built-in bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input, and parasitic effects are almost completely eliminated.
- 2) Only the on / off conditions need to be set for operation, making device design easy.
- 3) Higher mounting densities can be achieved.

●Circuit schematic



E : Emitter
C : Collector
B : Base

●Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	50	—	—	V	$I_c=50\ \mu\text{A}$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	—	V	$I_c=1\text{mA}$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_e=72\ \mu\text{A}$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{\text{CB}}=50\text{V}$
Emitter cutoff current	I_{EBO}	30	—	58	μA	$V_{\text{EB}}=4\text{V}$
Collector-emitter saturation voltage	$\text{V}_{\text{CE}(\text{sat})}$	—	—	0.3	V	$I_c=5\text{mA}, I_b=0.25\text{mA}$
DC current transfer ratio	h_{FE}	82	—	—	—	$I_c=5\text{mA}, V_{\text{CE}}=5\text{V}$
Emitter-base resistance	R	70	100	130	k Ω	—
Transition frequency	f _T	—	250	—	MHz	$V_{\text{CE}}=10\text{V}, I_e=-5\text{mA}, f=100\text{MHz}$ *

●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_c	100	mA
Collector power dissipation	P _C	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{tsg}	-55~+150	°C

●Package, marking, and packaging specifications

Part No.	DTC115GUA	DTC115GKA
Package	UMT3	SMT3
Marking	K29	K29
Packaging code	T106	T146
Basic ordering unit (pieces)	3000	3000